

N-channel 30 V 3.4 mΩ logic level MOSFET in D2PAK

12 October 2012

Product data sheet

### 1. Product profile

### 1.1 General description

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### **1.2 Features and benefits**

- Enhanced forward biased safe operating area for superior linear mode operation
- Very low Rdson for low conduction losses

### 1.3 Applications

- Electronic fuse
- Hot swap
- Load switch
- Soft start

### 1.4 Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	-	120	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	178	W
Static chara	acteristics	·					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12		-	2.95	3.4	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12		-	4.25	5	mΩ
Dynamic ch	naracteristics	·					
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; Fig. 14; Fig. 15		-	12.2	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; Fig. 14; Fig. 15		-	81	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup}$ ≤ 30 V; unclamped; $R_{GS}$ = 50 Ω; Fig. 3		-	-	246	mJ

[1] Capped at 120A due to package

# 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain[1]		
3	S	source		G-UFA
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

[1] It is not possible to make connection to pin 2.

### 3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN3R4-30BLE	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

### 4. Marking

Table 4.   Marking codes	
Type number	Marking code
PSMN3R4-30BLE	PSMN3R4-30BLE

### 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	30	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	30	V
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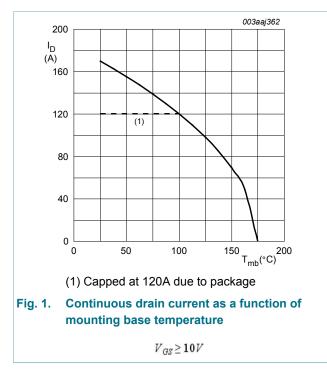
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# PSMN3R4-30BLE

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Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>		-	119	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	120	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 4		-	672	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	178	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	672	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} \texttt{=} \texttt{10 V}; \ T_{j(init)}\texttt{=} \texttt{25 °C}; \ I_{D}\texttt{=} \texttt{120 A}; \\ V_{sup} \texttt{\leq} \texttt{30 V}; \ unclamped; \ R_{GS}\texttt{=} \texttt{50 } \Omega; \\ \hline Fig. 3 \end{array}$		-	246	mJ

[1] Capped at 120A due to package



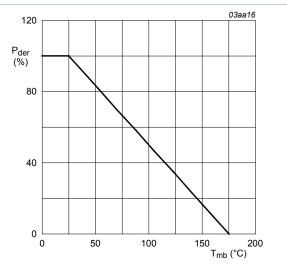


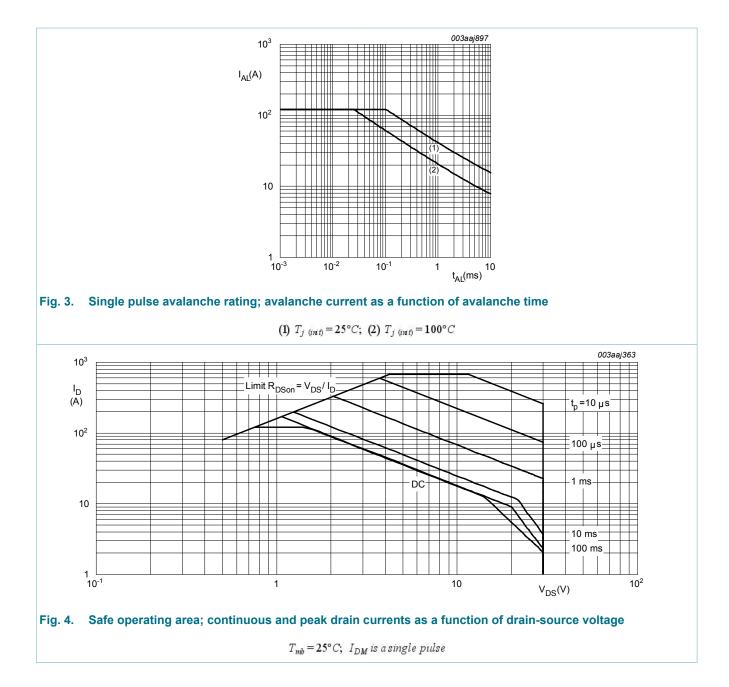
Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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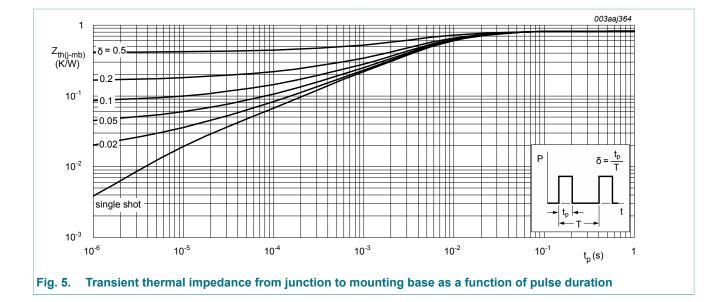
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### 6. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	0.73	0.84	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; FR4 board		-	50	-	K/W

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### 7. Characteristics

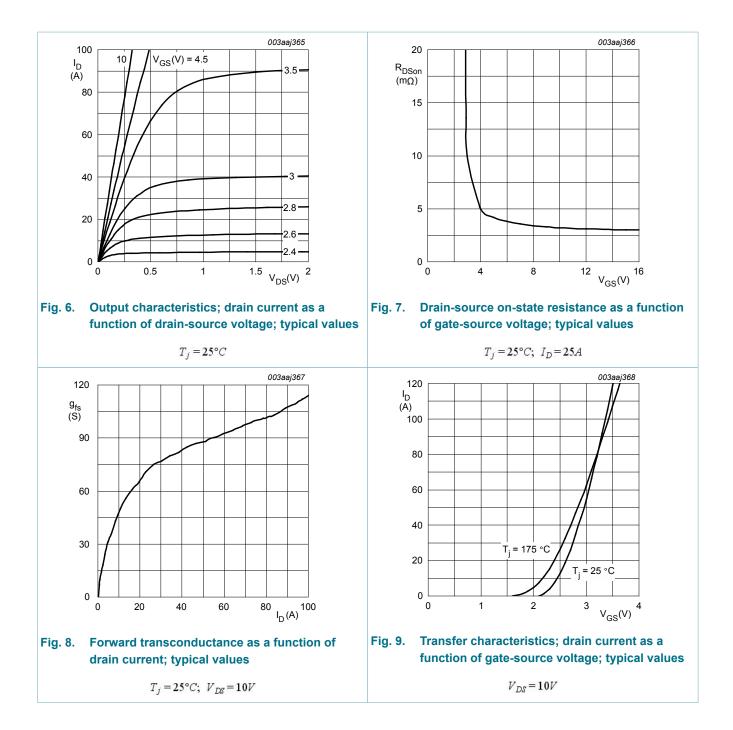
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	27	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <u>Fig. 10</u>	0.5	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <u>Fig. 11; Fig. 10</u>	1.3	1.7	2.15	V
	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 10	-	-	2.45	V	
I <sub>DSS</sub> drain leakage current	$V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.2	5	μA	
		$V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_j$ = 100 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	2.95	3.4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 13; Fig. 12	-	-	5.1	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	4.25	5	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 13; Fig. 12	-	-	6.5	mΩ

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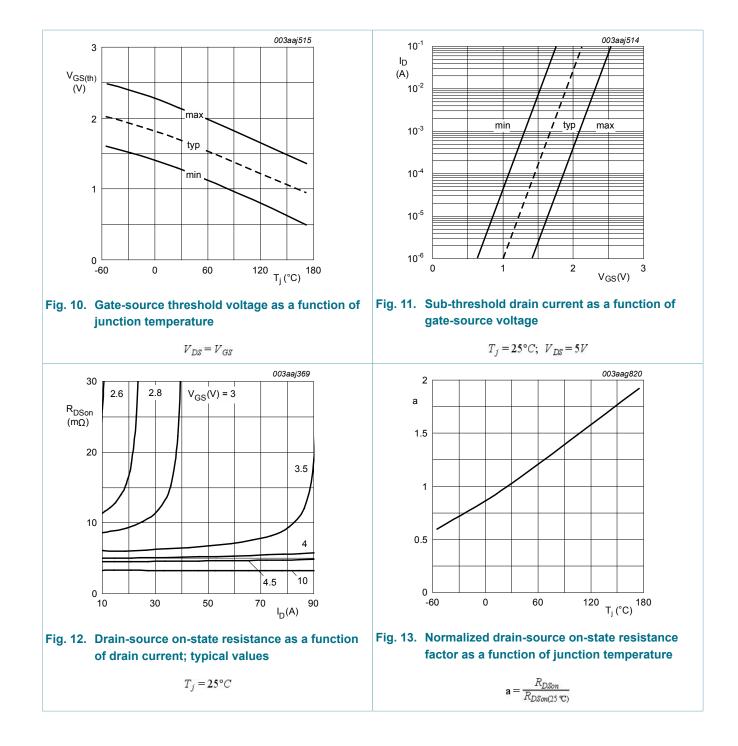
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	0.5	1	2	Ω
Dynamic ch	aracteristics		l.	1		
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	81	-	nC
		I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; Fig. 14; Fig. 15	-	37	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	79	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D$ = 25 A; $V_{DS}$ = 15 V; $V_{GS}$ = 4.5 V;	-	13.9	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 14; Fig. 15	-	7.5	-	nC
$Q_{GS(th-pl)}$	post-threshold gate- source charge		-	6.4	-	nC
Q <sub>GD</sub>	gate-drain charge		-	12.2	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; <u>Fig. 14; Fig. 15</u>	-	3.2	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	4682	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	909	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	438	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; R <sub>L</sub> = 0.6 Ω; V <sub>GS</sub> = 4.5 V;	-	35.7	-	ns
tr	rise time	R <sub>G(ext)</sub> = 4.7 Ω; T <sub>j</sub> = 25 °C	-	101	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	49	-	ns
t <sub>f</sub>	fall time		-	51.2	-	ns
Source-drai	n diode		1	1	1	
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; Fig. 17	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{\rm S}$ = 25 A; dI <sub>S</sub> /dt = 100 A/µs; V <sub>GS</sub> = 0 V;	-	37	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 15 V	-	38	-	nC

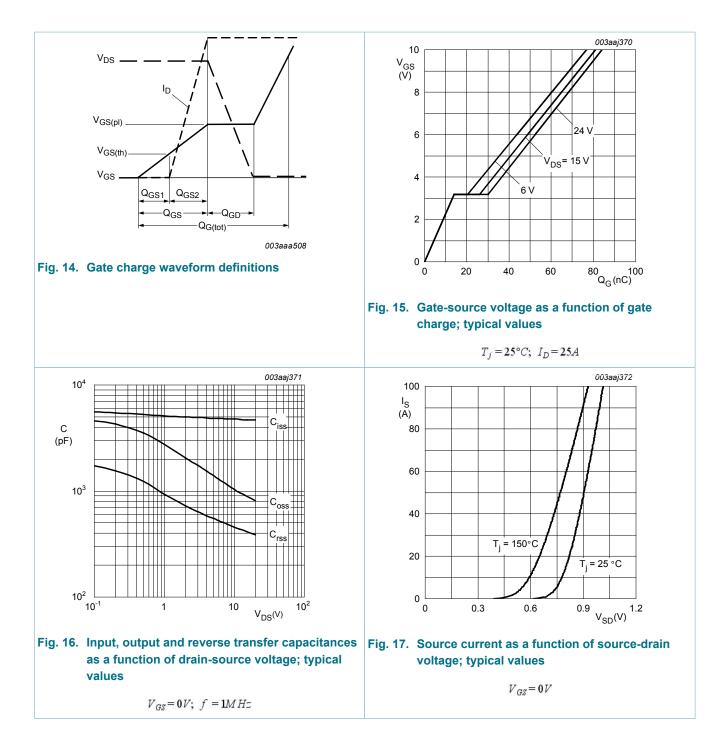
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### N-channel 30 V 3.4 m $\Omega$ logic level MOSFET in D2PAK



#### N-channel 30 V 3.4 m $\Omega$ logic level MOSFET in D2PAK

### 8. Package outline

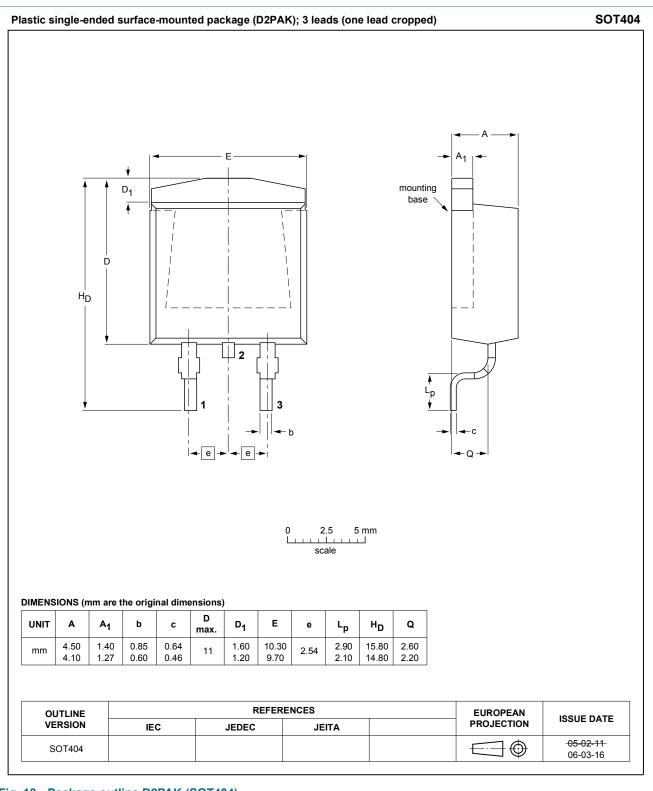


Fig. 18. Package outline D2PAK (SOT404)

PSMN3R4-30BLE

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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